

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 40 A, 1200 V, D3, TO-247-2L

NDSH40120C-F155

Description

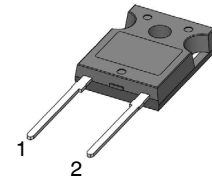
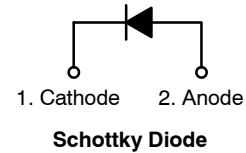
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 251 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Halogen Free/BFR Free and are RoHS Compliant

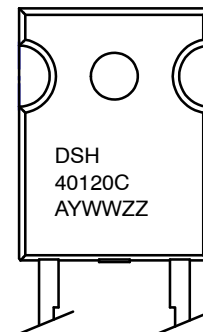
Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



TO-247-2LD
CASE 340DC

MARKING DIAGRAM



DSH40120C	= Specific Device Code
A	= Assembly Plant Code
YWW	= Date Code (Year & Week)
ZZ	= Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NDSH40120C–F155

ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{RRM}	Peak Repetitive Reverse Voltage		1200	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		251	mJ
I _F	Continuous Rectified Forward Current @ T _C < 143°C		40	A
	Continuous Rectified Forward Current @ T _C < 135°C		46	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1295	A
		T _C = 150°C, 10 μs	1274	A
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	195	A
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	73	A
P _{tot}	Power Dissipation	T _C = 25°C	366	W
		T _C = 150°C	61	W
T _J , T _{STG}	Operating and Storage Temperature Range		−55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 251 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 31.7 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max	0.41	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F = 40 A, T _J = 25°C	–	1.4	1.75	V
		I _F = 40 A, T _J = 125°C	–	1.66	–	
		I _F = 40 A, T _J = 175°C	–	1.9	–	
I _R	Reverse Current	V _R = 1200 V, T _J = 25°C	–	9	200	μA
		V _R = 1200 V, T _J = 125°C	–	22	200	
		V _R = 1200 V, T _J = 175°C	–	46	200	
Q _C	Total Capacitive Charge	V = 800 V	–	184	–	nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz	–	2840	–	pF
		V _R = 400 V, f = 100 kHz	–	159	–	
		V _R = 800 V, f = 100 kHz	–	115	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
NDSH40120C–F155	DSH40120C	TO–247–2LD (Pb-Free / Halogen Free)	30 Units / Tube

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

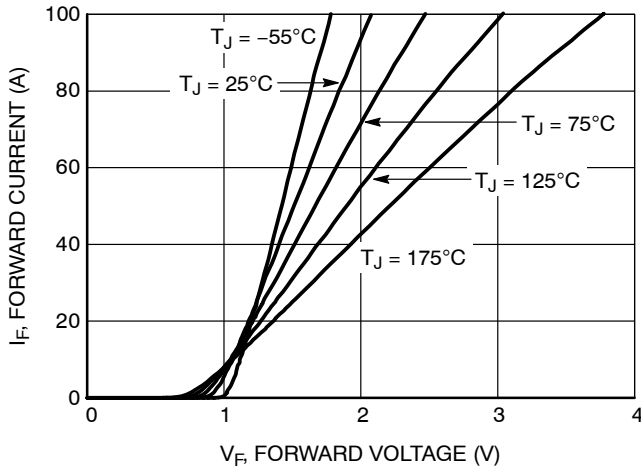


Figure 1. Forward Characteristics

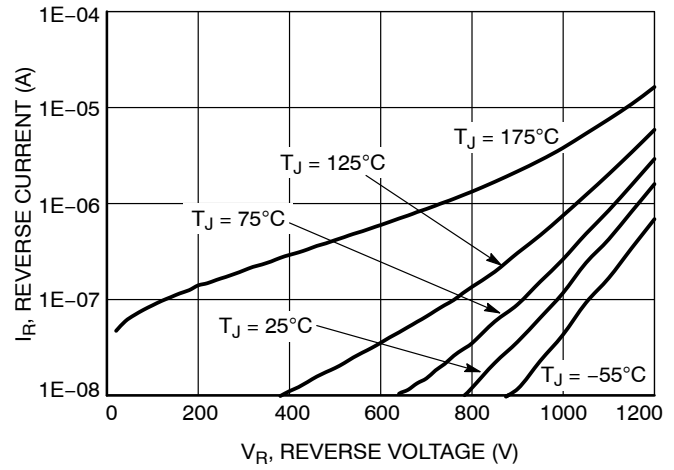


Figure 2. Reverse Characteristics

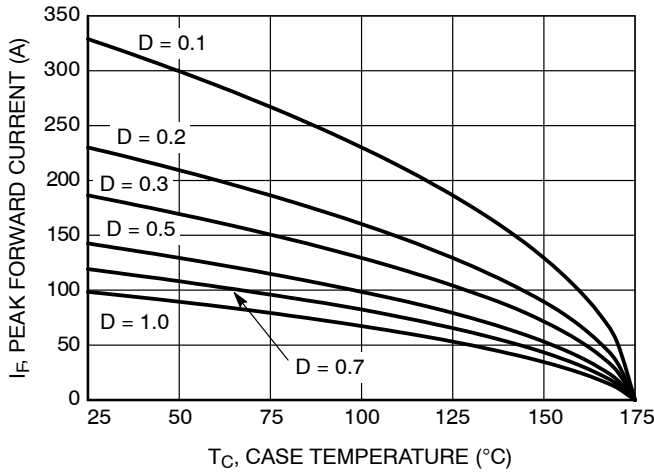


Figure 3. Current Derating

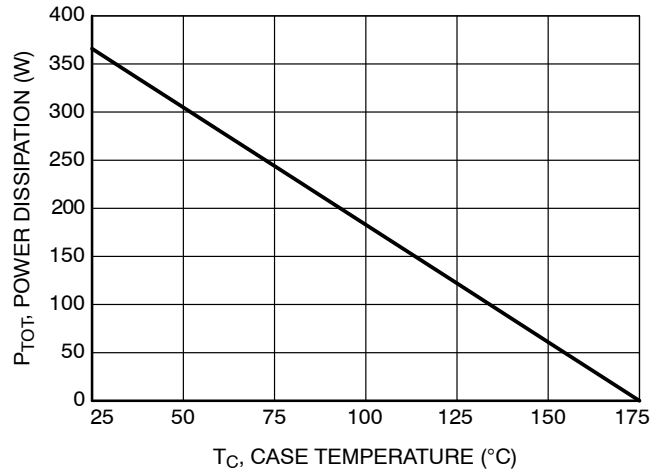


Figure 4. Power Derating

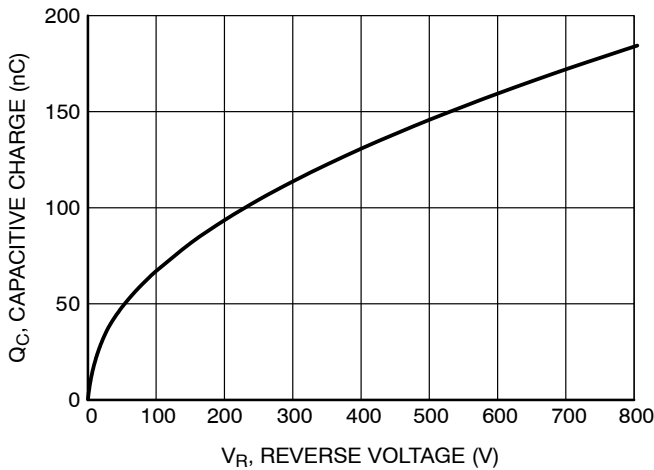


Figure 5. Capacitive Charge vs. Reverse Voltage

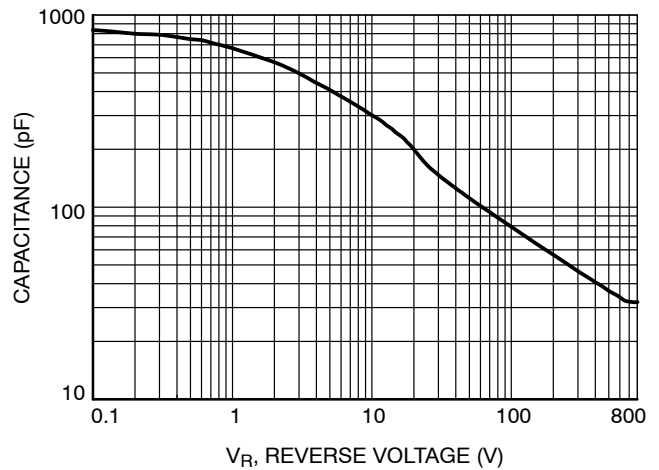


Figure 6. Capacitive vs. Reverse Voltage

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

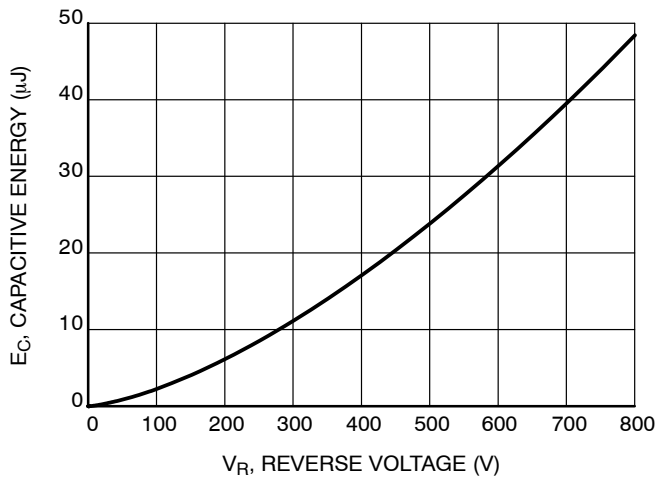


Figure 7. Capacitance Stored Energy

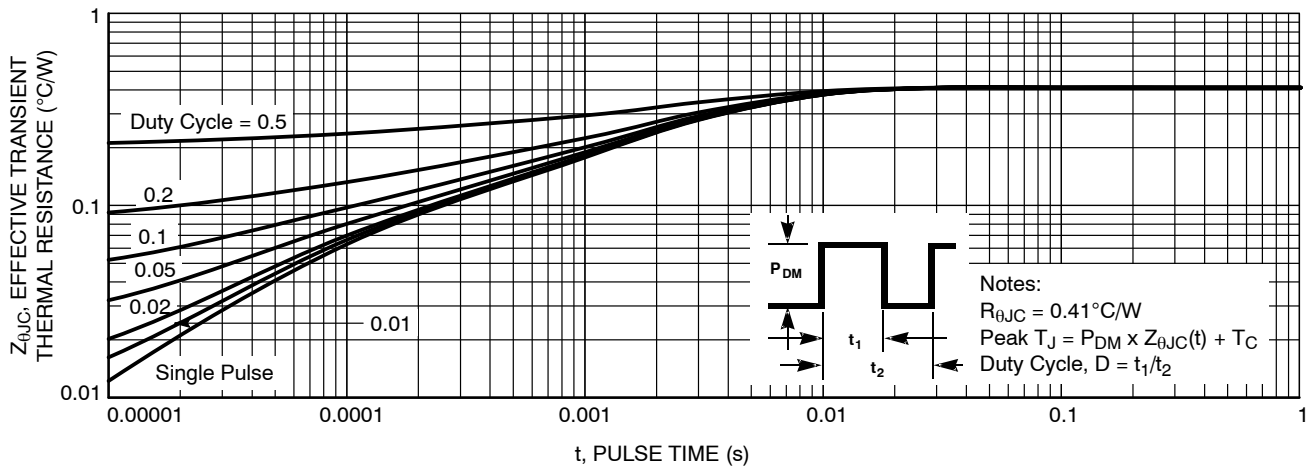
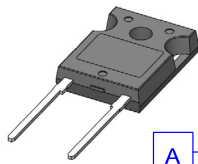
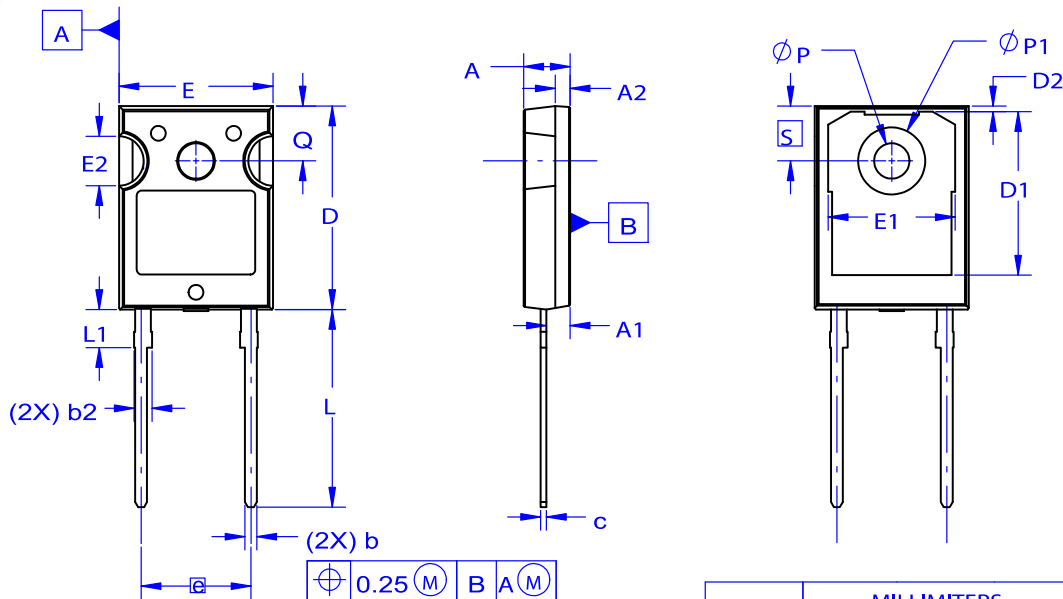


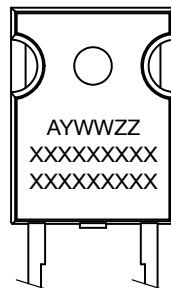
Figure 8. Junction-to-Case Transient Thermal Response Curve


TO-247-2LD
CASE 340DC
ISSUE O

DATE 09 JUL 2020


NOTES:

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*


XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.60	1.72	1.84
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	11.12	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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